FIG. 1A

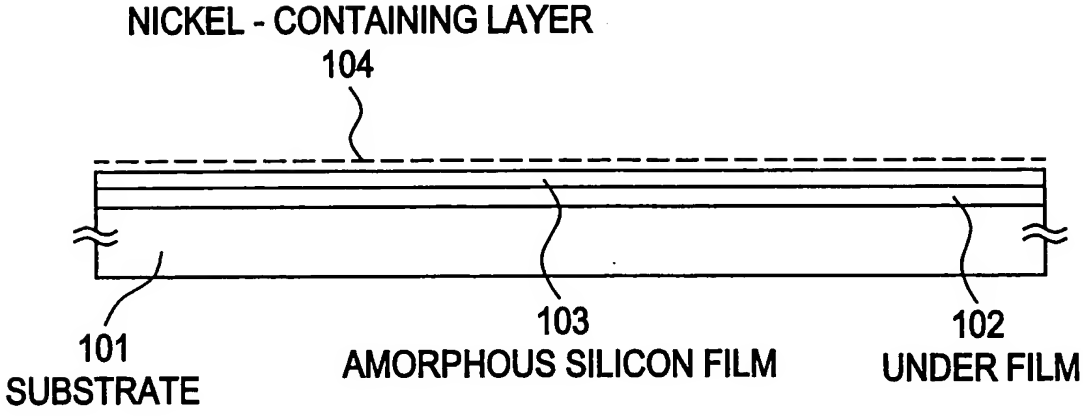


FIG. 1B

LASER CRYSTALLIZATION STEP

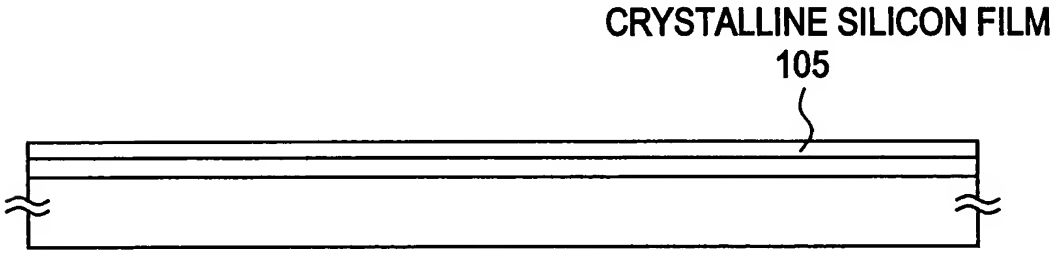


FIG. 1C

THERMAL TREATMENT STEP IN REDUCING ATMOSPHERE

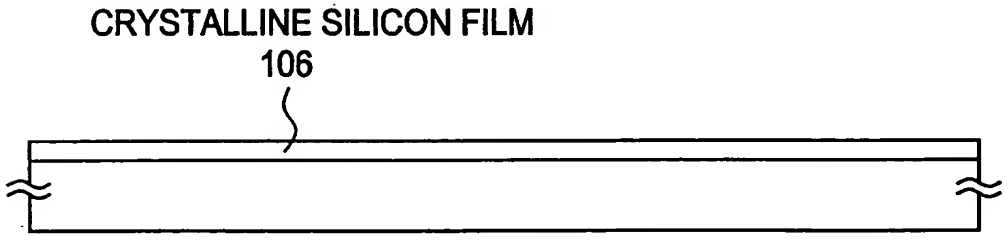


FIG. 2A

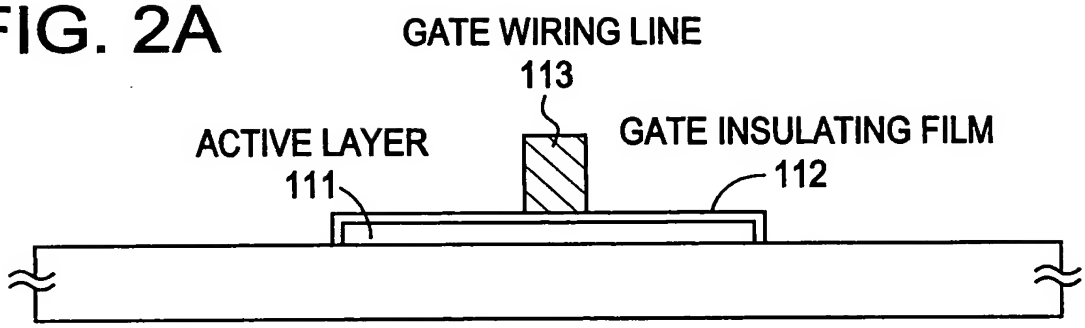


FIG. 2B

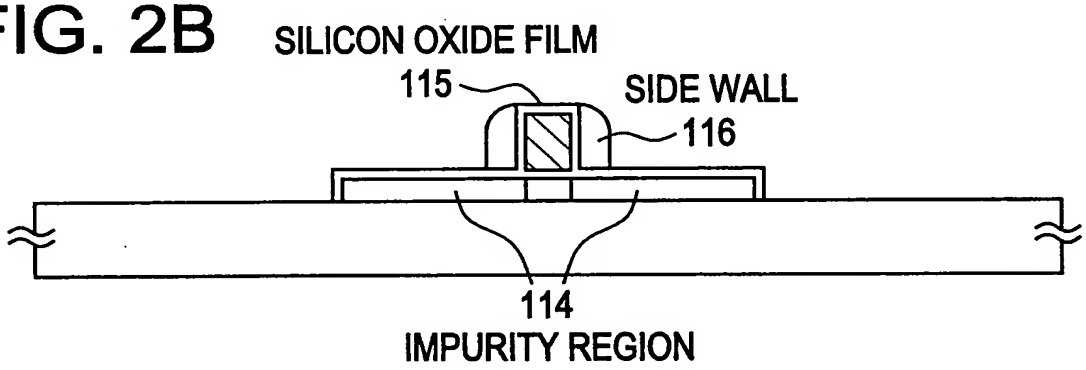


FIG. 2C

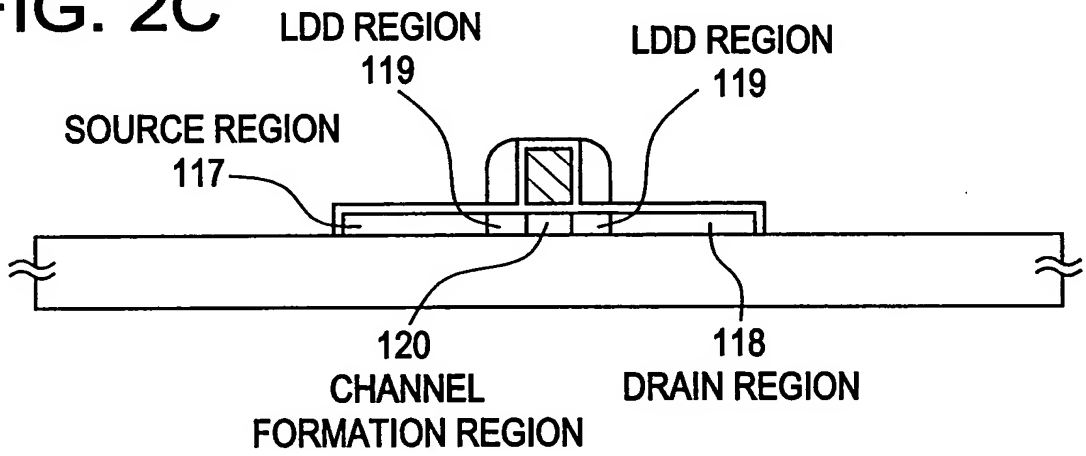


FIG. 2D

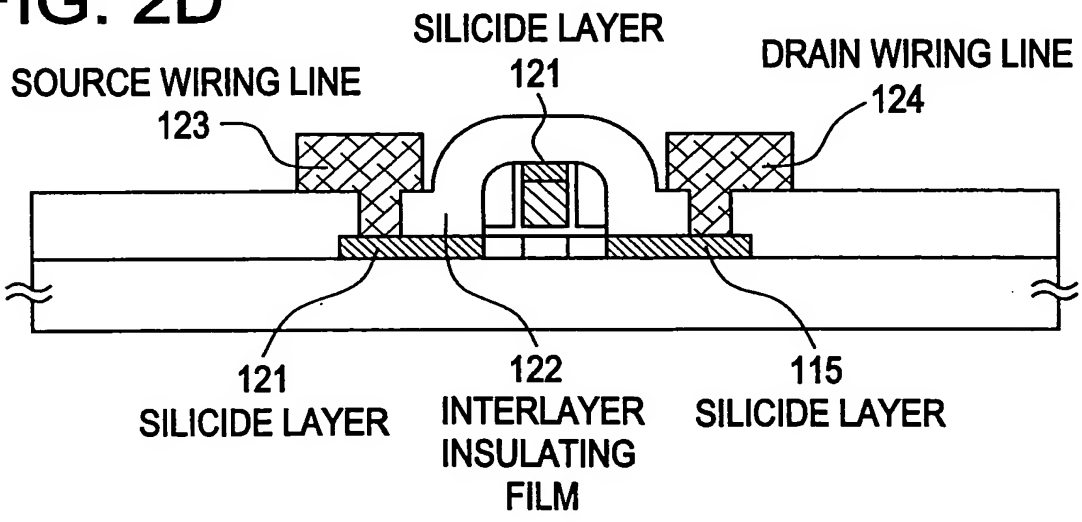


FIG. 3A

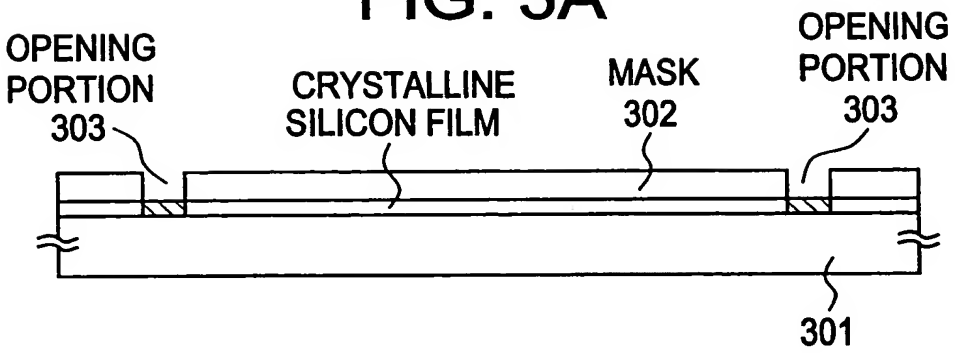
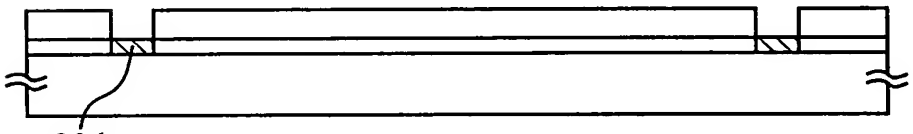


FIG. 3B

ADDING STEP OF PHOSPHORUS



GETTERING REGION

FIG. 3C

CRYSTALLINE SILICON FILM
305

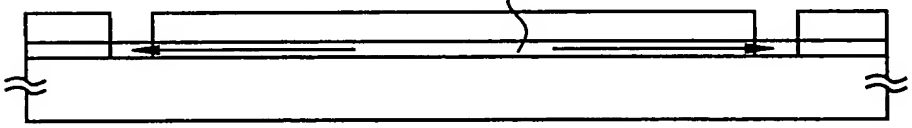


FIG. 3D

HEAT TREATMENT STEP IN REDUCING ATMOSPHERE

ACTIVE LAYER
306
ACTIVE LAYER
307

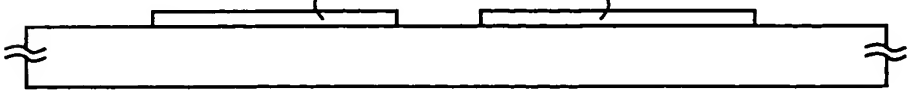


FIG. 4A

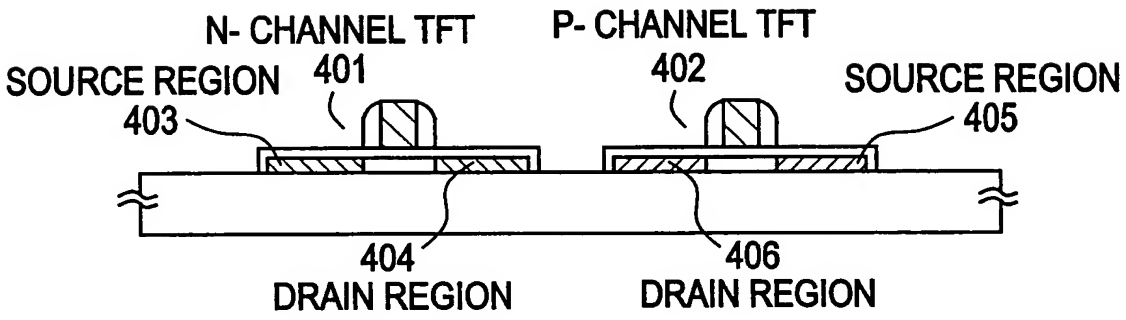


FIG. 4B

GETTERING STEP

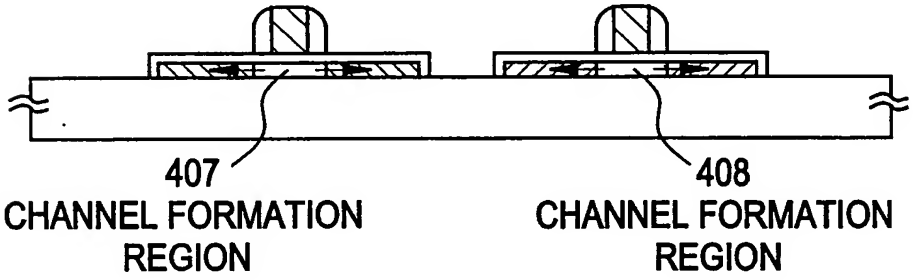
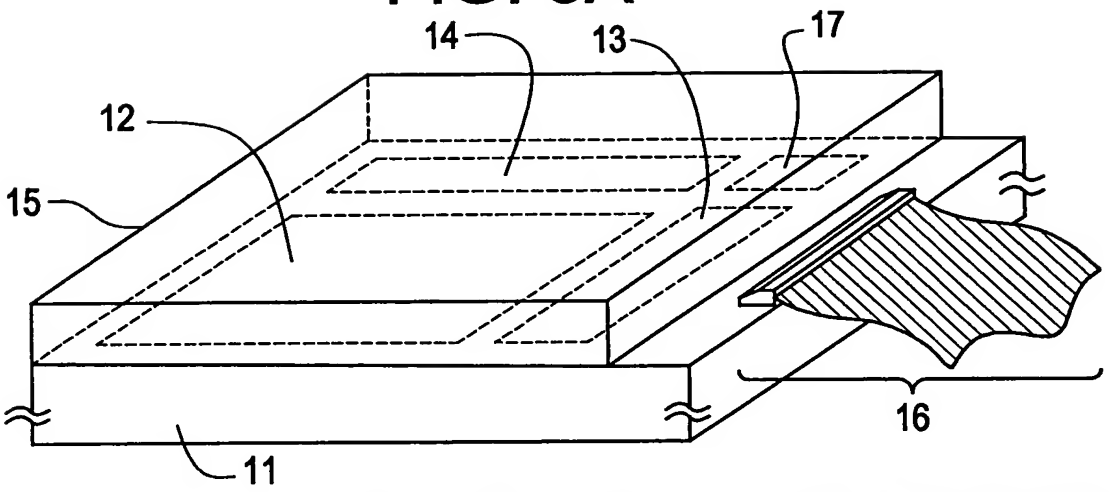


FIG. 5A



11: SUBSTRATE HAVING INSULATING SURFACE
12: PIXEL MATRIX CIRCUIT
13: SOURCE DRIVER CIRCUIT
14: GATE DRIVER CIRCUIT
15: OPPOSITE SUBSTRATE
16: FPC
17: SIGNAL PROCESSING CIRCUIT

FIG. 5B

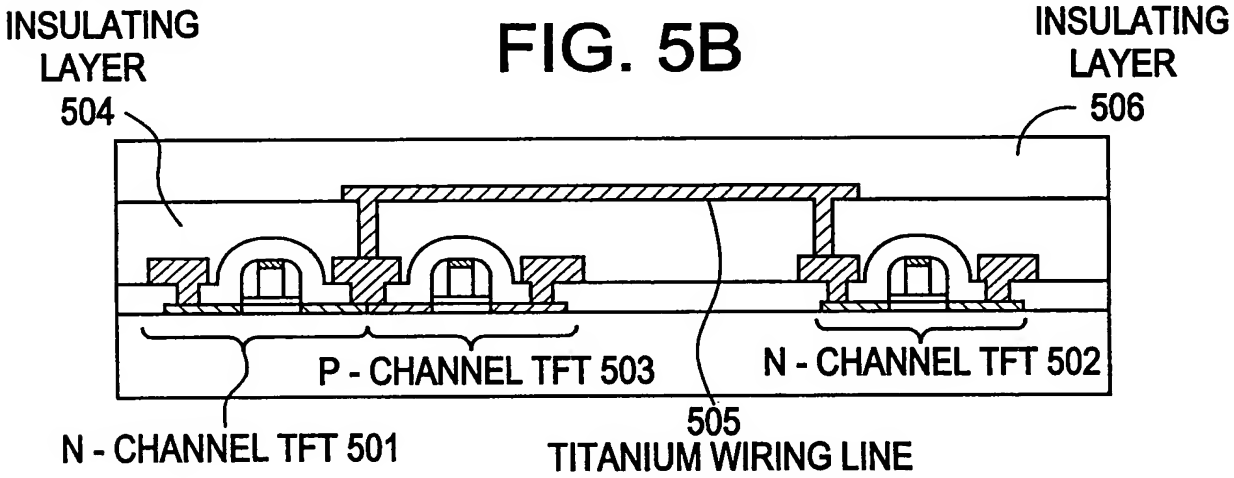


FIG. 5C

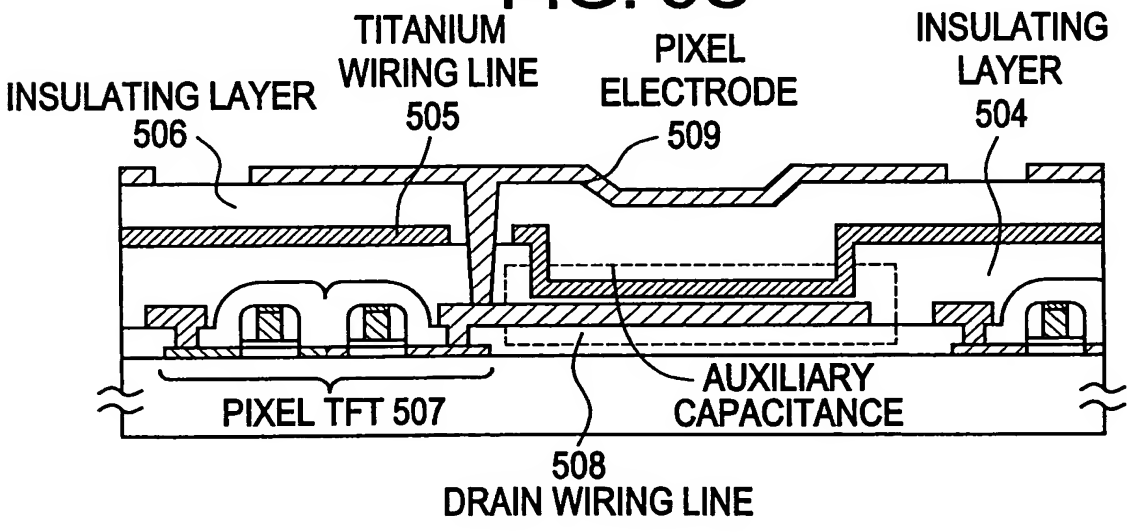


FIG. 6

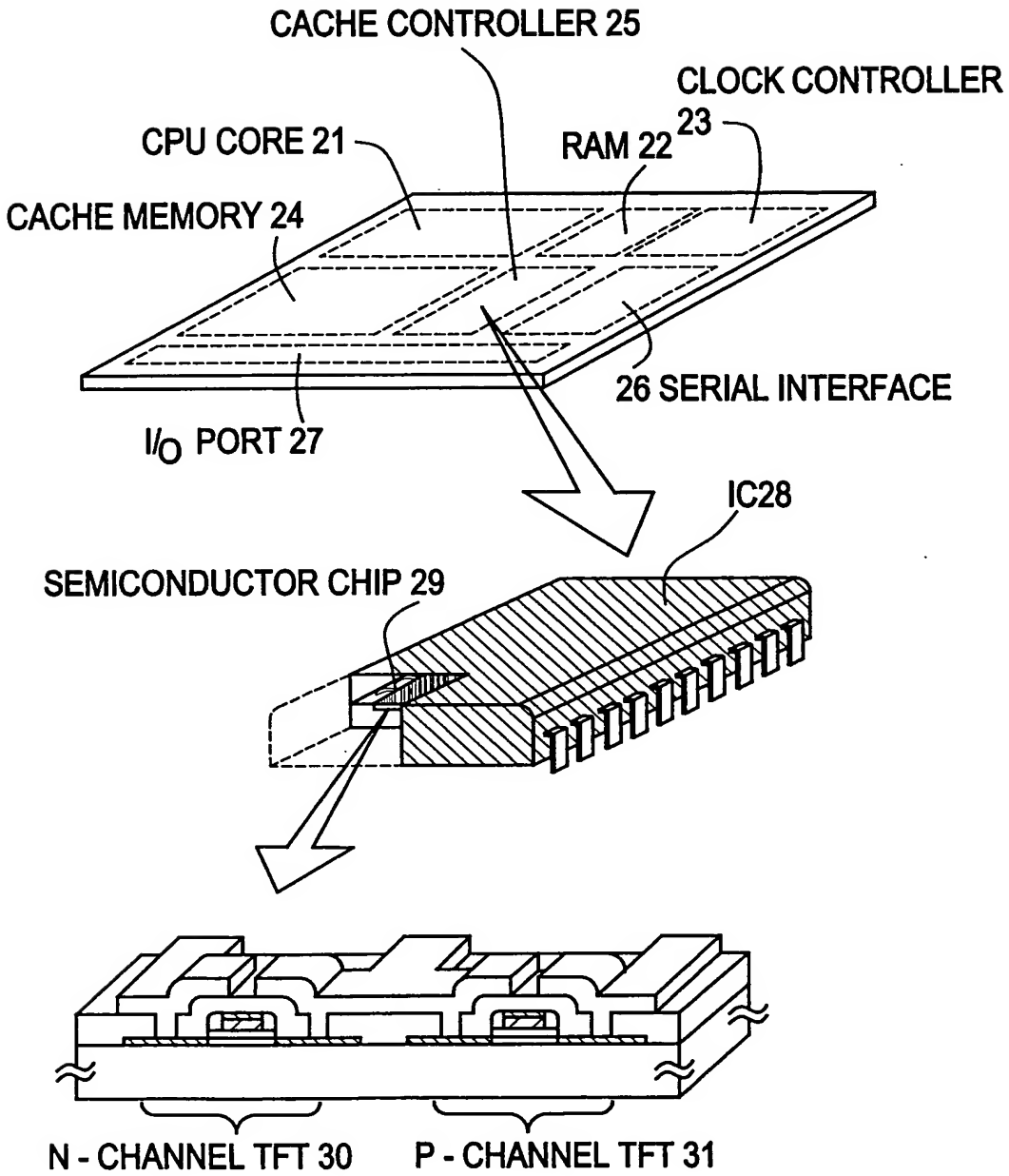

CACHE CONTROLLER 25
CLOCK CONTROLLER 23
CPU CORE 21
RAM 22
CACHE MEMORY 24
26 SERIAL INTERFACE
I/O PORT 27
IC28
SEMICONDUCTOR CHIP 29
N - CHANNEL TFT 30
P - CHANNEL TFT 31

FIG. 7A

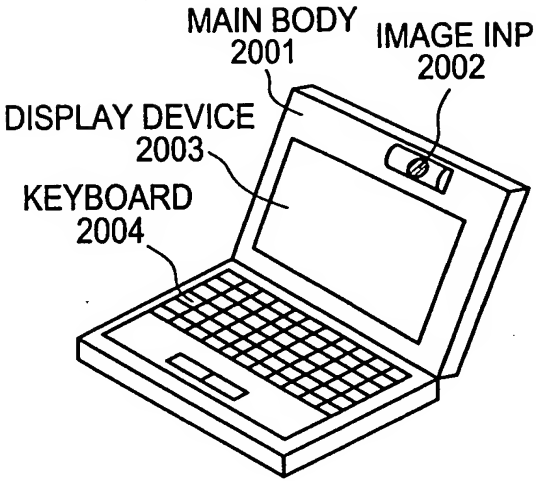


FIG. 7B

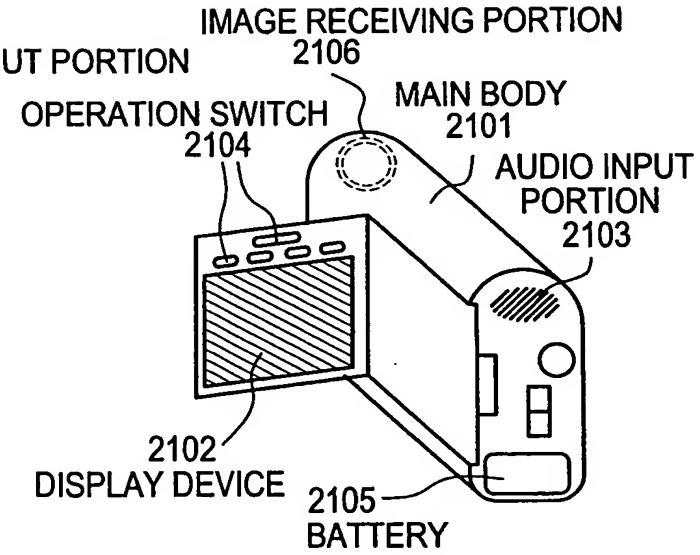


FIG. 7C

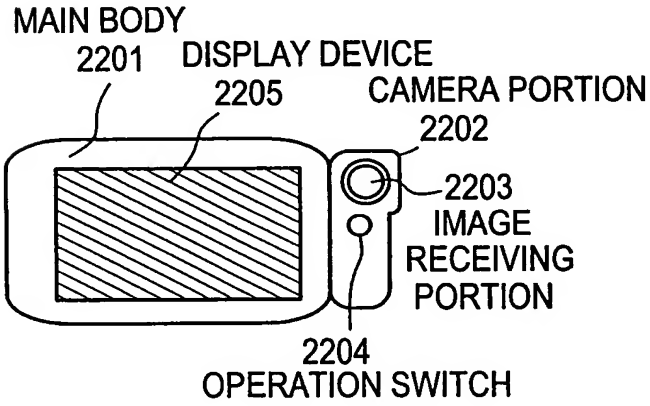


FIG. 7D

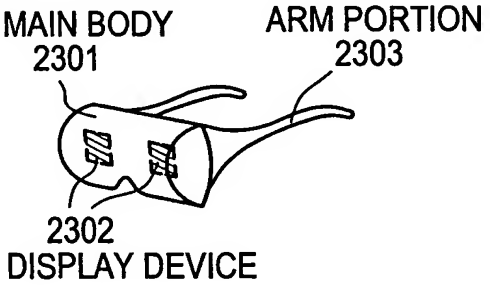


FIG. 7E

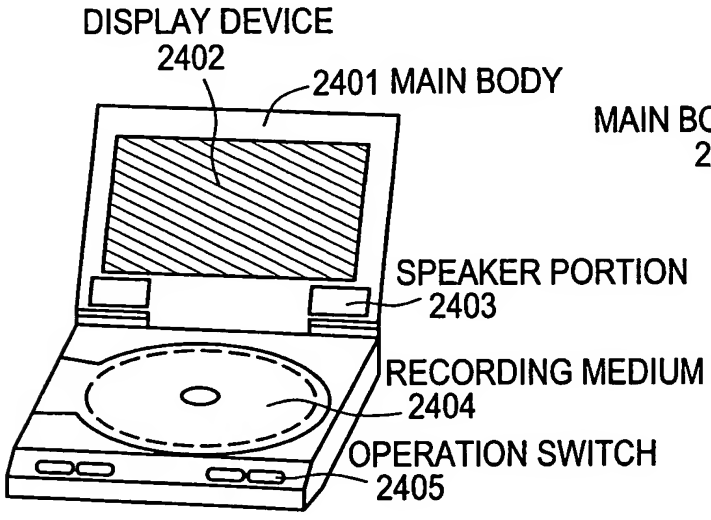


FIG. 7F

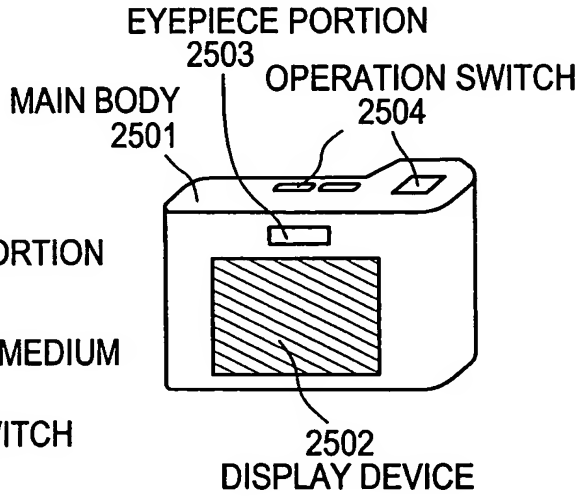


FIG. 8A

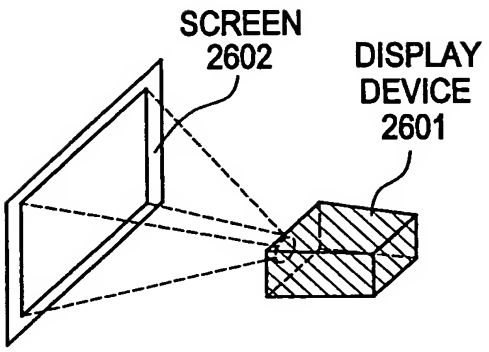


FIG. 8B

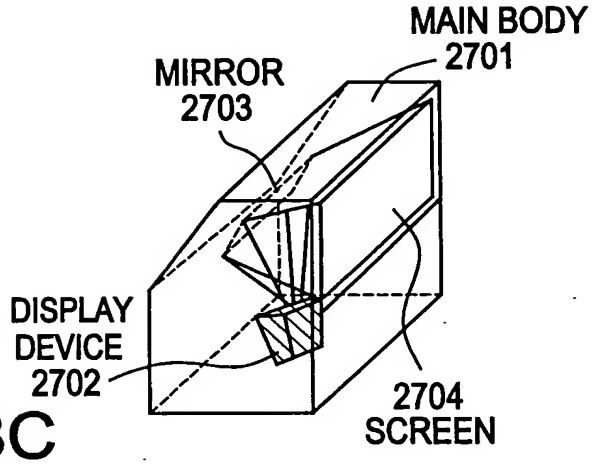


FIG. 8C

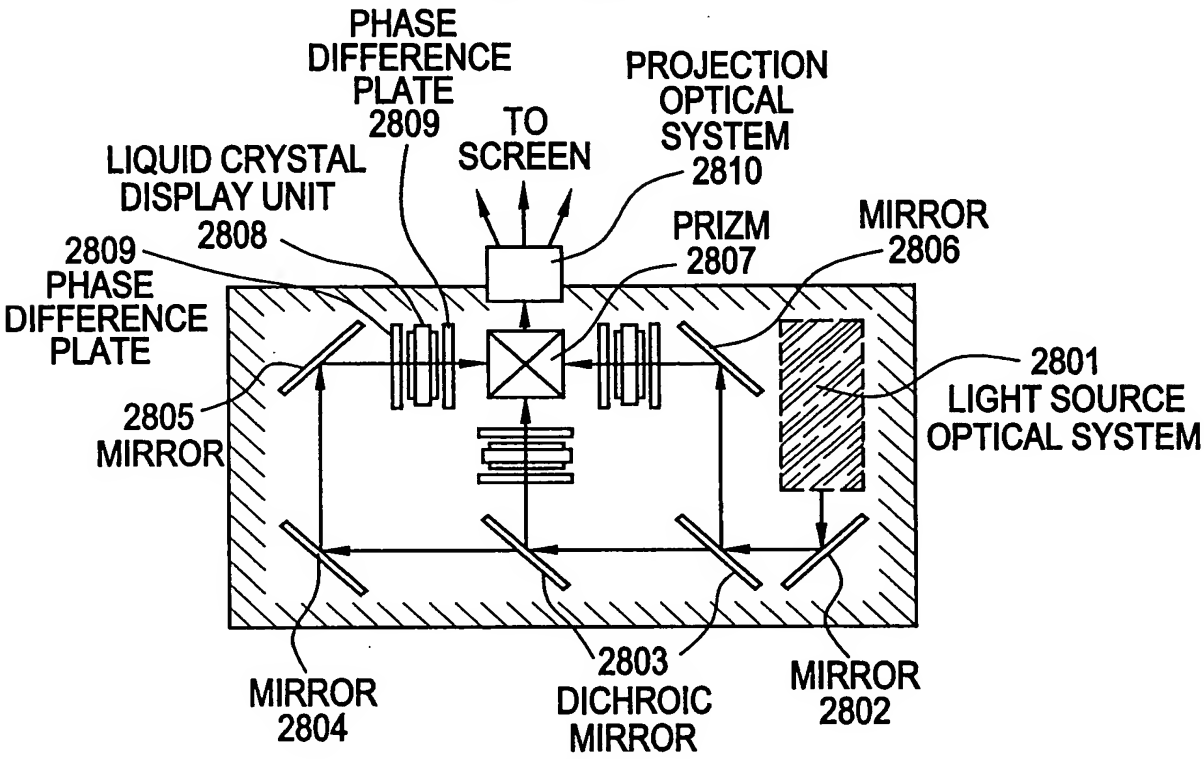


FIG. 8D

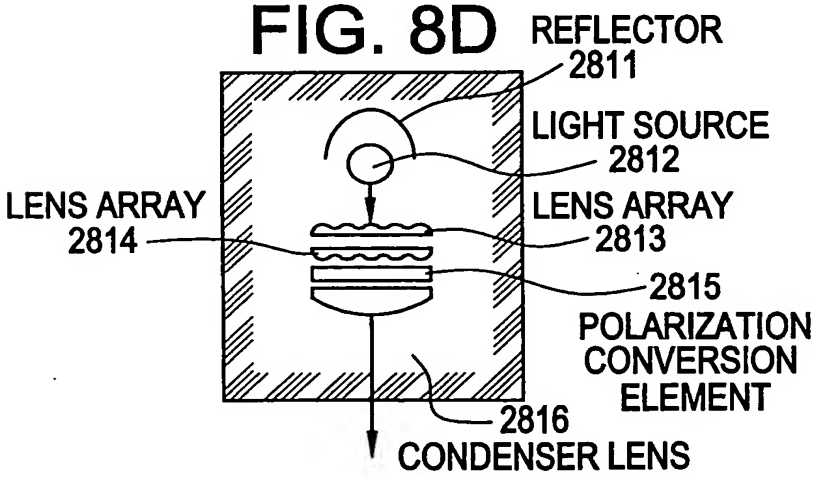


FIG. 9A

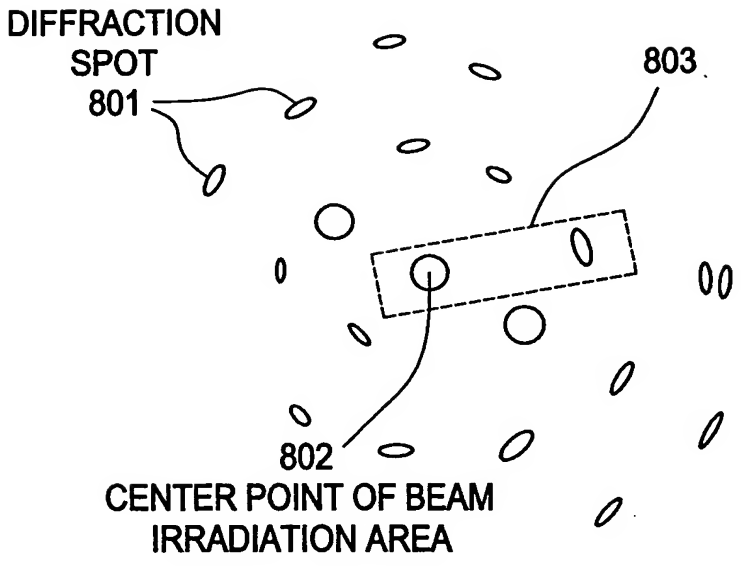

DIFFRACTION
SPOT
801
803
802
CENTER POINT OF BEAM
IRRADIATION AREA

FIG. 9B

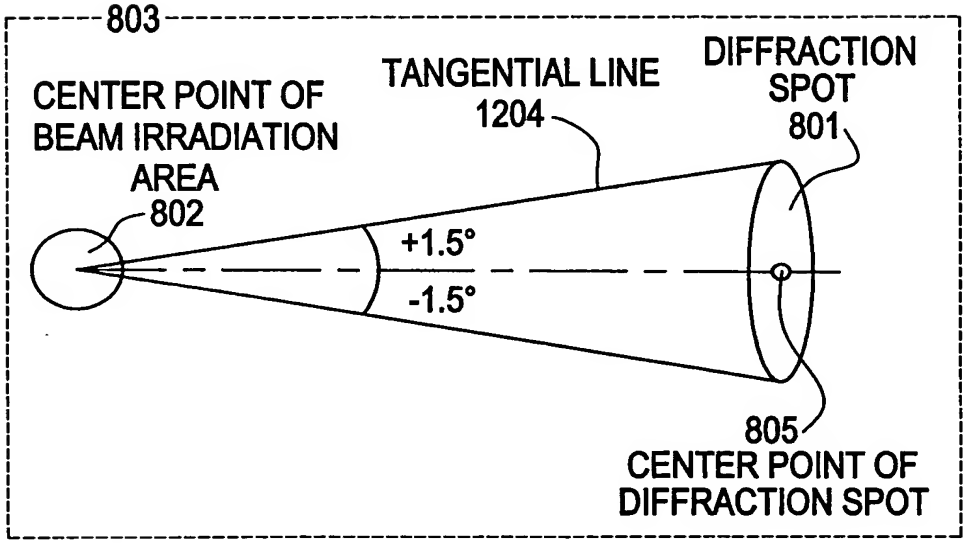

803
CENTER POINT OF
BEAM IRRADIATION
AREA
802
TANGENTIAL LINE
1204
DIFFRACTION
SPOT
801
+1.5°
-1.5°
805
CENTER POINT OF
DIFFRACTION SPOT

FIG. 10

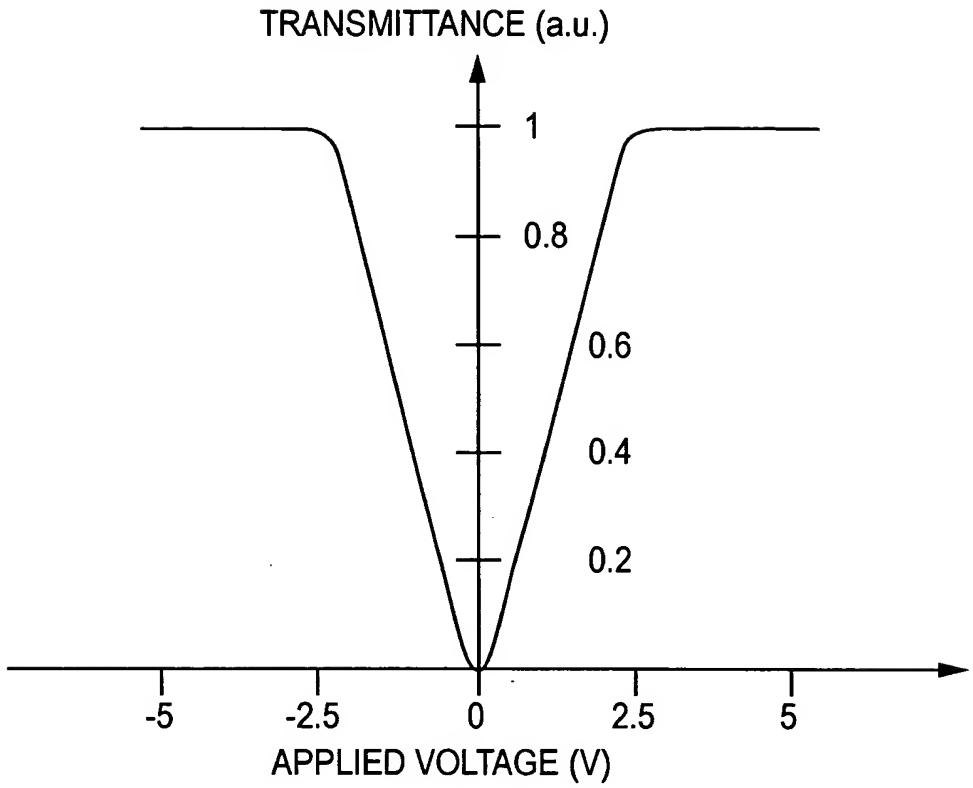
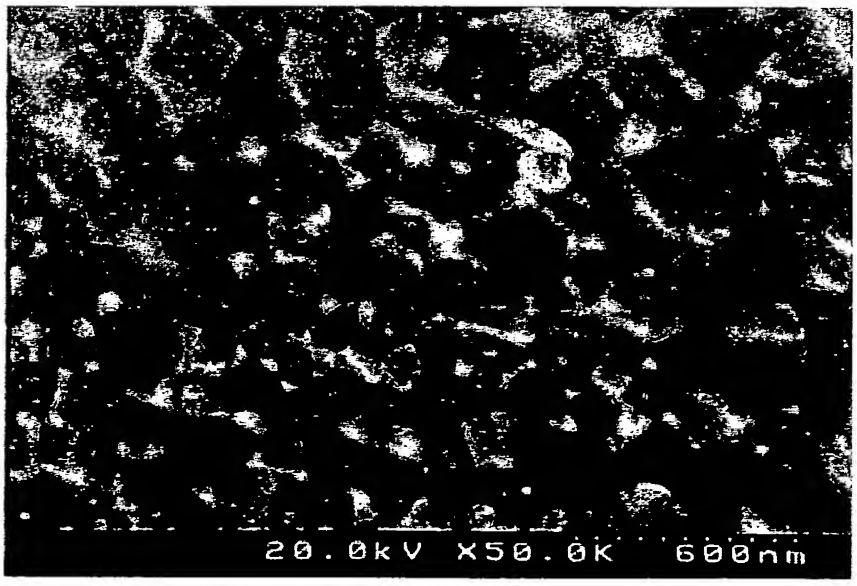
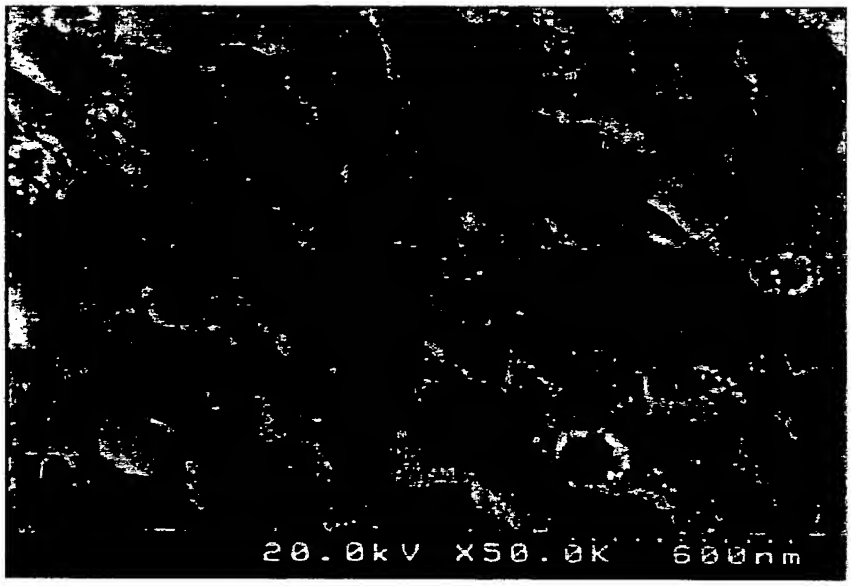


FIG. 11



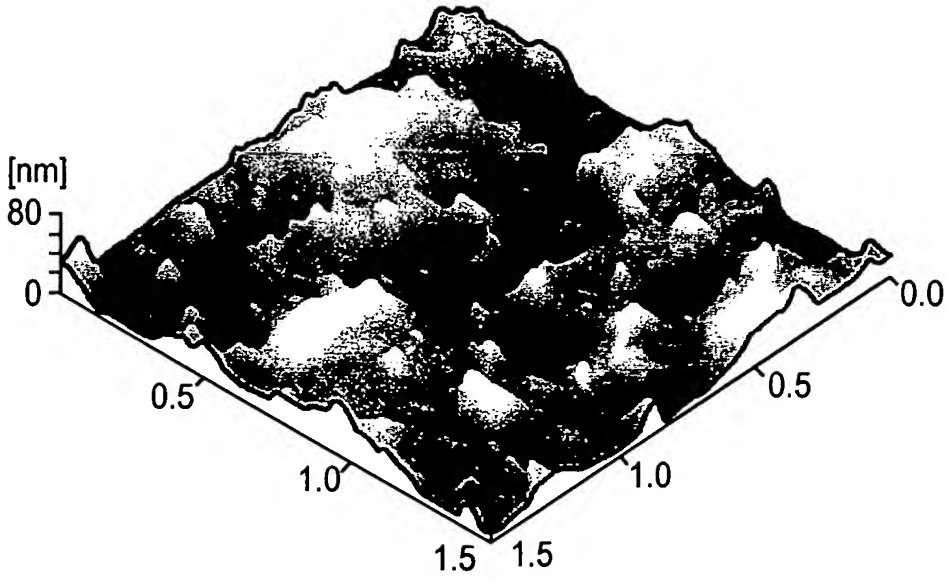
BEFORE HIGH TEMPERATURE ANNEALING

FIG. 12



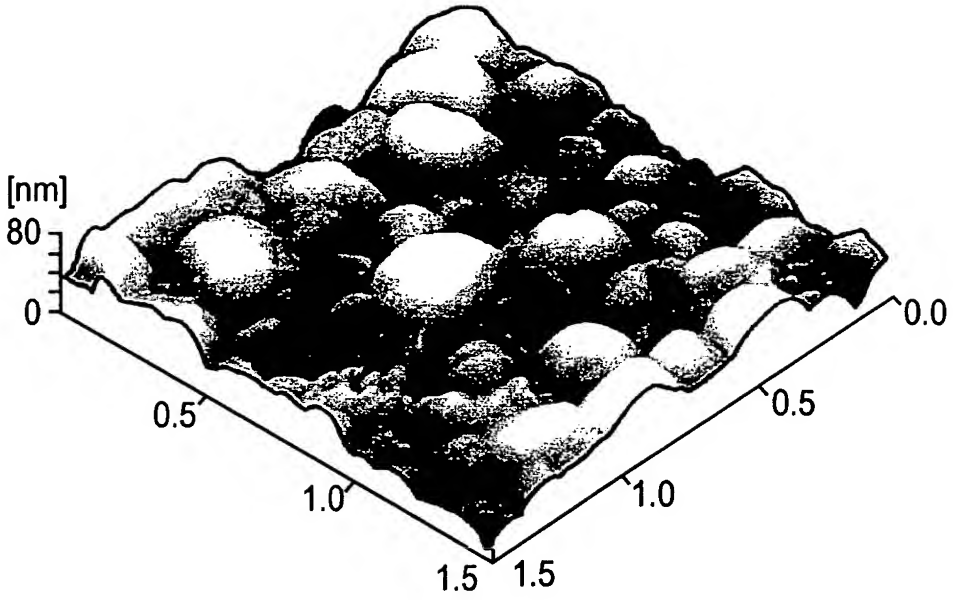
AFTER HIGH TEMPERATURE ANNEALING

FIG. 13



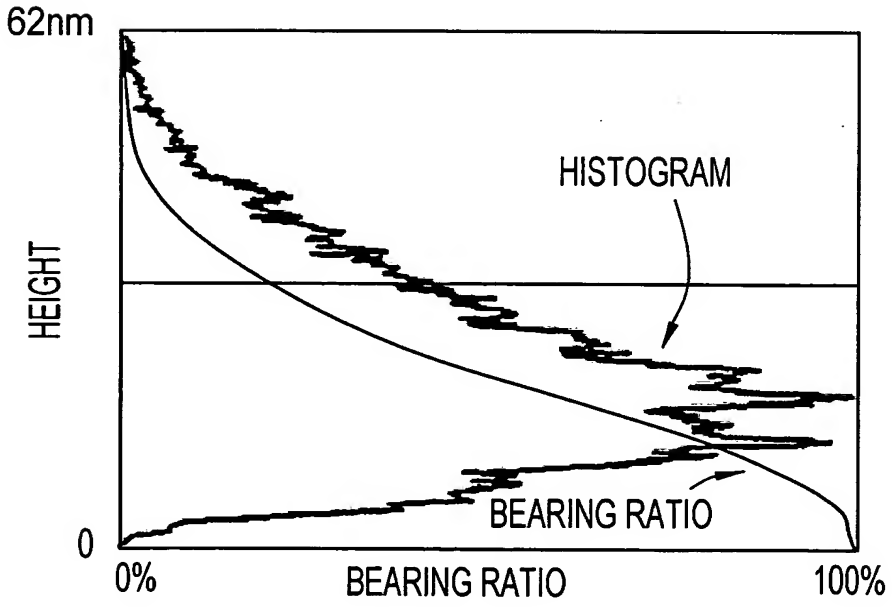
BEFORE HIGH TEMPERATURE ANNEALING

FIG. 14



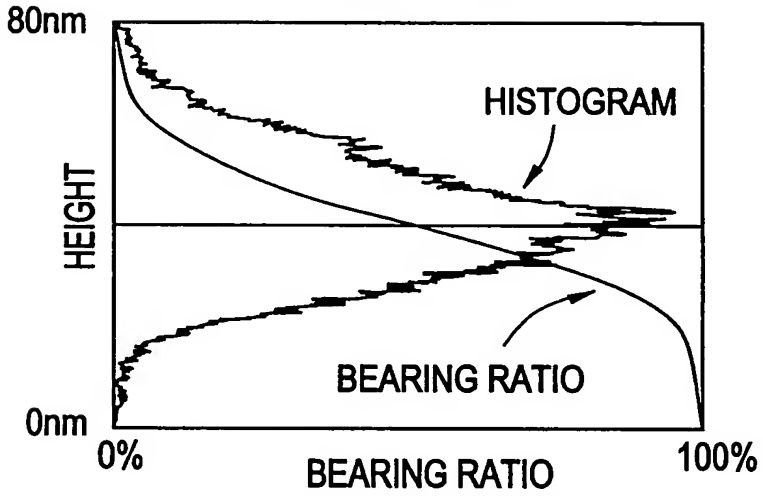
AFTER HIGH TEMPERATURE ANNEALING

FIG. 15



BEFORE HIGH TEMPERATURE ANNEALING

FIG. 16



AFTER HIGH TEMPERATURE ANNEALING

FIG. 17

OBSERVATION REGION	BEFORE HIGH TEMPERATURE ANNEALING	AFTER HIGH TEMPERATURE ANNEALING
1	13.623	40.925
2	20.027	51.126
3	20.629	59.364
4	21.798	48.539
5	16.666	55.341
6	15.097	46.510
7	13.120	57.655
8	14.035	51.120
9	12.599	54.416
10	20.699	36.945
MINIMUM VALUE (%)	12.60	36.95
MAXIMUM VALUE (%)	21.80	59.36
AVERAGE VALUE (%)	16.83	50.19
STANDARD DEVIATION σ	3.61	7.18

BEARING RATIO AT 2^{-1}(P-V VALUE) (%)